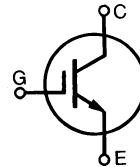


HiPerFAST™ IGBT

IXGH 40N60B
IXGT 40N60B

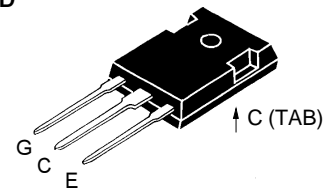
$V_{CES} = 600 \text{ V}$
 $I_{C25} = 75 \text{ A}$
 $V_{CE(sat)} = 2.1 \text{ V}$
 $t_{fi} = 180 \text{ ns}$

Preliminary data sheet

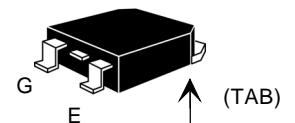


Symbol	Test Conditions	Maximum Ratings		
V_{CES}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}$	600	V	
V_{CGR}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}; R_{GE} = 1 \text{ M}\Omega$	600	V	
V_{GES}	Continuous	± 20	V	
V_{GEM}	Transient	± 30	V	
I_{C25}	$T_C = 25^\circ\text{C}$	75	A	
I_{C110}	$T_C = 110^\circ\text{C}$	40	A	
I_{CM}	$T_C = 25^\circ\text{C}, 1 \text{ ms}$	150	A	
SSOA (RBSOA)	$V_{GE} = 15 \text{ V}, T_{VJ} = 125^\circ\text{C}, R_G = 10 \Omega$ Clamped inductive load, $L = 100 \mu\text{H}$	$I_{CM} = 80$ @ $0.8 V_{CES}$	A	
P_c	$T_C = 25^\circ\text{C}$	250	W	
T_J		-55 ... +150	$^\circ\text{C}$	
T_{JM}		150	$^\circ\text{C}$	
T_{stg}		-55 ... +150	$^\circ\text{C}$	
Maximum lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		300	$^\circ\text{C}$	
M_d	Mounting torque (M3)	1.13/10Nm/lb.in.		
Weight		TO-247 AD	6	g
		TO-247 SMD	4	g

TO-247 AD
(IXGH)



TO-268 (D3)
(IXGT)



G = Gate, C = Collector,
E = Emitter, TAB = Collector

Features

- International standard packages JEDEC TO-268 surface mountable and JEDEC TO-247 AD
- High current handling capability
- Latest generation HDMOS™ process
- MOS Gate turn-on - drive simplicity

Applications

- AC motor speed control
- DC servo and robot drives
- DC choppers
- Uninterruptible power supplies (UPS)
- Switched-mode and resonant-mode power supplies

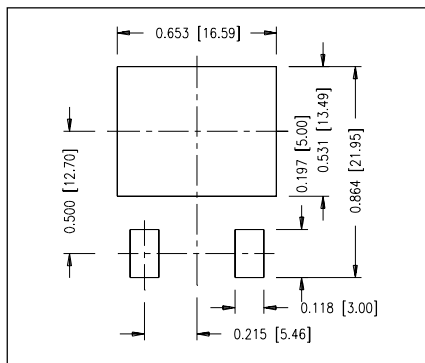
Advantages

- Space savings (two devices in one package)
- High power density
- Suitable for surface mounting
- Switching speed for high frequency applications
- Easy to mount with 1 screw, TO-247 (isolated mounting screw hole)

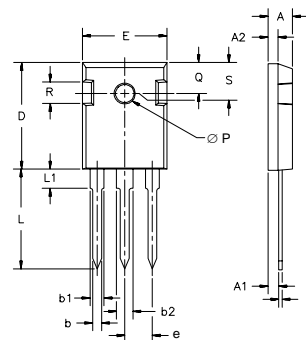
Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
BV_{CES}	$I_C = 250 \mu\text{A}, V_{GE} = 0 \text{ V}$ BV_{CES} temperature coefficient	600	0.072	V %/K
$V_{GE(th)}$	$I_C = 250 \mu\text{A}, V_{CE} = V_{GE}$ $V_{GE(th)}$ temperature coefficient	2.5	-0.286	V %/K
I_{CES}	$V_{CE} = 0.8 \cdot V_{CES}$ $V_{GE} = 0 \text{ V}$ $T_J = 25^\circ\text{C}$ $T_J = 150^\circ\text{C}$			200 μA 1 mA
I_{GES}	$V_{CE} = 0 \text{ V}, V_{GE} = \pm 20 \text{ V}$			$\pm 100 \text{ nA}$
$V_{CE(sat)}$	$I_C = I_{C110}, V_{GE} = 15 \text{ V}$	1.6	2.1	V

Symbol	Test Conditions	Characteristic Values		
		(T _J = 25°C, unless otherwise specified)		
		min.	typ.	max.
g_{fs}	I_C = I_{C110}, V_{CE} = 10 V, Pulse test, t ≤ 300 μs, duty cycle ≤ 2 %	30	42	S
C_{ies}	V_{CE} = 25 V, V_{GE} = 0 V, f = 1 MHz		3300	pF
C_{oes}			310	pF
C_{res}			65	pF
Q_g	I_C = I_{C110}, V_{GE} = 15 V, V_{CE} = 0.5 V_{CES}		116	nC
Q_{ge}			23	nC
Q_{gc}			55	nC
t_{d(on)}	Inductive load, T_J = 25°C I_C = I_{C110}, V_{GE} = 15 V V_{CE} = 0.8 V_{CES}, R_G = R_{off} = 4.7 Ω Remarks: Switching times may increase for V _{CE} (Clamp) > 0.8 • V _{CES} , higher T _J or increased R _G		25	ns
t_{ri}			30	ns
t_{d(off)}			180	300 ns
t_{fi}			180	270 ns
E_{off}			2.7	4.0 mJ
t_{d(on)}	Inductive load, T_J = 125°C I_C = I_{C110}, V_{GE} = 15 V V_{CE} = 0.8 V_{CES}, R_G = R_{off} = 4.7 Ω Remarks: Switching times may increase for V _{CE} (Clamp) > 0.8 • V _{CES} , higher T _J or increased R _G		25	ns
t_{ri}			35	ns
E_{on}			0.4	mJ
t_{d(off)}			300	ns
t_{fi}			270	ns
E_{off}			4.0	mJ
R_{thJC}	(IXGH40N60B)			0.50 KW
R_{thCK}			0.25	KW

Min Recommended Footprint

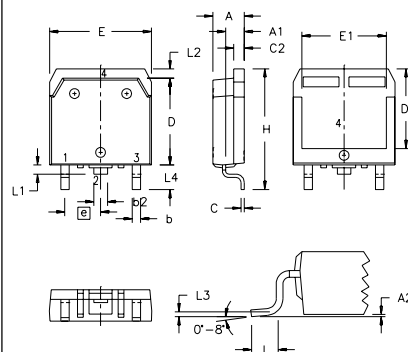


TO-247 AD Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A ₁	2.2	2.54	.087	.102
A ₂	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b ₁	1.65	2.13	.065	.084
b ₂	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
⊙P	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15	BSC	.242	BSC

TO-268 Outline



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.193	.201	4.90	5.10
A1	.106	.114	2.70	2.90
A2	.001	.010	0.02	0.25
b	.045	.057	.115	.145
b2	.075	.083	1.90	2.10
C	.016	.026	0.40	0.65
C2	.057	.063	1.45	1.60
D	.543	.551	13.80	14.00
D1	.488	.500	12.40	12.70
E	.624	.632	15.85	16.05
E1	.524	.535	13.30	13.60
e	.215 BSC		5.45 BSC	
H	.736	.752	18.70	19.10
L	.094	.106	2.40	2.70
L1	.047	.055	1.20	1.40
L2	.039	.045	1.00	1.15
L3	.010 BSC		0.25 BSC	
L4	.150	.161	3.80	4.10

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,881,106	5,017,508	5,049,961	5,187,117	5,486,715
	4,850,072	4,931,844	5,034,796	5,063,307	5,237,481	5,381,025